Elektronische Bauelemente

2SC4738-C

0.15A, 60V

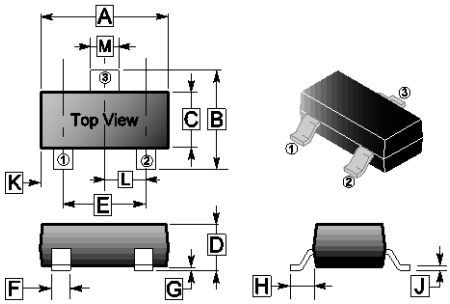
NPN Plastic Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- High Voltage and High Current
- High DC Current Gain
- Complementary to 2SA1832-C

SOT-523



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.50	1.70	G	-	0.10
B	1.45	1.75	H	0.55 REF.	
C	0.70	0.90	J	0.08	0.20
D	0.60	0.90	K	-	
E	0.90	1.10	L	0.50 TYP.	
F	0.15	0.35	M	0.25	0.40

CLASSIFICATION OF h_{FE}

Product-Rank	2SC4738-GR-C	2SC4738-BL-C
Range	200~400	350~700
Marking	LG	LL

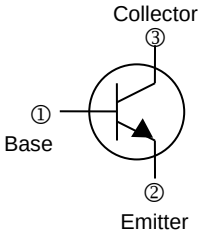
PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-523	3K	7 inch

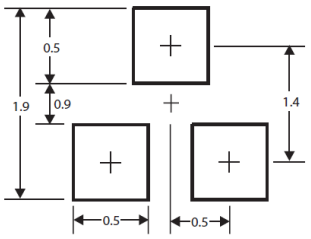
ORDER INFORMATION

Part Number	Type
2SC4738-□□-C	Lead (Pb)-free and Halogen-free

***□=h_{FE} Mark**



Mounting Pad Layout



*Dimensions in millimeters

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current-Continuous	I_C	150	mA
Collector Power Dissipation	P_C	100	mW
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	1250	°C/W
Junction & Storage Temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	-	-	V	I_C=100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	50	-	-	V	I_C=1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	-	-	V	I_E=100μA, I_C=0
Collector Cut-off Current	I_{CBO}	-	-	100	nA	V_{CB}=60V, I_E=0
Emitter Cut-off Current	I_{EBO}	-	-	100	nA	V_{EB}=5V, I_C=0
DC Current Gain	h_{FE}	200	-	700		V_{CE}=6V, I_C=2mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.25	V	I_C=100mA, I_B=10mA
Transition Frequency	f_T	80	-	-	MHz	V_{CE}=10V, I_C=1mA
Collector Output Capacitance	C_{ob}	-	3.5	-	pF	V_{CB}=10V, I_E=0, f=1MHz

Elektronische Bauelemente

2SC4738-C

0.15A, 60V

NPN Plastic Encapsulated Transistor

CHARACTERISTICS CURVE